

MA6X128

Silicon epitaxial planar type

For switching circuits

Features

- Four-element contained in one package, allowing high-density mounting
- Centrosymmetrical wiring, allowing to free from the taping direction
- The mirror image wiring of (MA6X123)
- Short reverse recovery time t_{rr}
- Small terminal capacitance, C_t
- High breakdown voltage ($V_R = 80$ V)

Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	80	V
Peak reverse voltage	V_{RM}	80	V
Forward current (DC)*1	I_F	100	mA
Peak forward current*1	I_{FM}	225	mA
Non-repetitive peak forward surge current*1,2	I_{FSM}	500	mA
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Note) *1 : Value for single diode

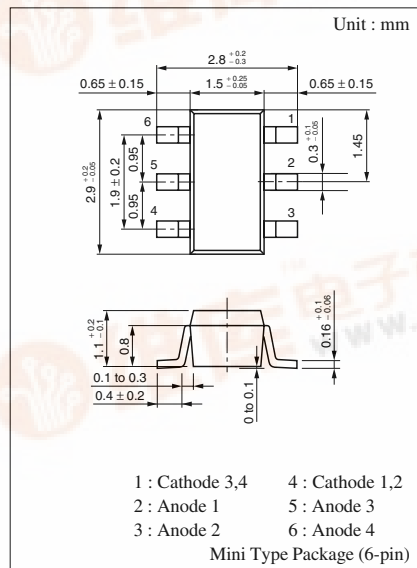
*2 : $t = 1$ s

Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	$V_R = 75$ V			100	nA
Forward voltage (DC)	V_F	$I_F = 100$ mA			1.2	V
Reverse voltage (DC)	V_R	$I_R = 100$ μA	80			V
Terminal capacitance	C_t	$V_R = 0$ V, $f = 1$ MHz			2	pF
Reverse recovery time*	t_{rr}	$I_F = 10$ mA, $V_R = 6$ V $I_{rr} = 0.1 \cdot I_R$, $R_L = 100$ Ω			3	ns

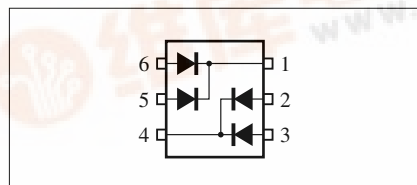
Note) 1. Rated input/output frequency: 100 MHz

2. * : t_{rr} measuring circuit



Marking Symbol: M2V

Internal Connection



Bias Application Unit N-50BU

